

## Features

- Saturated Power: 120 W
- Drain Efficiency: 70%
- Small Signal Gain: 17 dB
- Lead-Free Air Cavity Ceramic Package
- RoHS\* Compliant

## Applications

- Avionics - TACAN, DME, IFF
- Military Radio
- L, S-band Radar
- Electronic Warfare
- ISM
- General Amplification

## Description

The MAPC-A3010-AB is a 120 W packaged, unmatched transistor utilizing a high performance, 0.15  $\mu\text{m}$  GaN on SiC production process. This transistor supports both defense and commercial related applications.

Offered in a thermally-enhanced flange package, the MAPC-A3010-AB provides superior performance under CW operation allowing customers to improve SWaP-C benchmarks in their next generation systems.

## Typical RF Performance:

- Measured at CW =  $P_{\text{sat}}$ , defined at  $I_{\text{gs}} = 2.88 \text{ mA}$ .  
 $V_{\text{DS}} = 28 \text{ V}$ ,  $I_{\text{DQ}} = 1000 \text{ mA}$ ,  $T_{\text{C}} = 25^{\circ}\text{C}$

| Frequency (GHz) | Output Power (dBm) | Gain (dB) | $\eta_{\text{D}}$ (%) |
|-----------------|--------------------|-----------|-----------------------|
| 1.2             | 51.6               | 16.6      | 66.4                  |
| 1.3             | 51.8               | 17.2      | 69.4                  |
| 1.4             | 50.9               | 18.0      | 71.7                  |

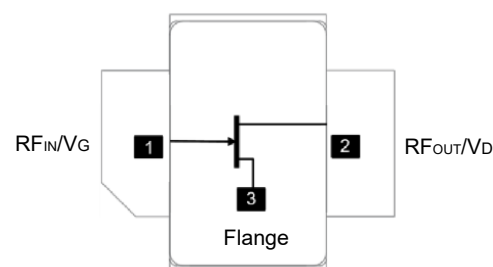
## Ordering Information

| Part Number      | MOQ Increment |
|------------------|---------------|
| MAPC-A3010-AB    | Bulk          |
| MAPC-A3010-ABSB1 | Sample Board  |



440223

## Functional Schematic



## Pin Configuration

| Pin # | Pin Name                                | Function          |
|-------|-----------------------------------------|-------------------|
| 1     | $\text{RF}_{\text{IN}} / V_{\text{G}}$  | RF Input / Gate   |
| 2     | $\text{RF}_{\text{OUT}} / V_{\text{D}}$ | RF Output / Drain |
| 3     | Flange <sup>1</sup>                     | Ground / Source   |

1. The flange on the package bottom must be connected to RF, DC and thermal ground.

\* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

**RF Electrical Specifications: Frequency = 1.3 GHz,  $P_{SAT}$  @  $I_{GS} = 2.88$  mA,  $T_A = +25^\circ\text{C}$ ,  $V_{DS} = 28$  V,  $I_{DQ} = 1000$  mA, Low Power Gain tested at  $P_{IN}$  of 10 dBm.**

| Parameter        | Symbol       | Min. | Typ. | Max. | Units |
|------------------|--------------|------|------|------|-------|
| Saturated Power  | $P_{SAT}$    | 123  | 143  | —    | W     |
| Drain Efficiency | $\eta_{SAT}$ | 62   | 67   | —    | %     |
| Low Power Gain   | $G_{SS}$     | 19.4 | 20.3 | —    | dB    |

Note: Final testing and screening for all transistor sales is performed using the MAPC-A3010-ABSB1 at 1.3 GHz.

## Absolute Maximum Ratings<sup>2,3</sup>

| Parameter                           | Absolute Maximum |
|-------------------------------------|------------------|
| Drain-Source Voltage                | 84 V             |
| Gate Voltage                        | -10 V, +2 V      |
| Drain Current                       | 12 A             |
| Gate Current                        | 29 mA            |
| Junction Temperature <sup>4,5</sup> | +225°C           |
| Operating Temperature               | -40°C to +65°C   |
| Storage Temperature                 | -55°C to +150°C  |
| Mounting Temperature                | +245°C           |

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.
- Operating at nominal conditions with  $T_J \leq +225^\circ\text{C}$  will ensure  $MTTF > 1 \times 10^6$  hours.
- Junction Temperature ( $T_J$ ) =  $T_C + \Theta_{JC} * (V * I)$   
Typical thermal resistance ( $\Theta_{JC}$ ) = 1.39 °C/W for CW.  
a) For  $T_C = +25^\circ\text{C}$ ,  
 $T_J = 185^\circ\text{C}$  @  $P_{DISS} = 115$  W  
b) For  $T_C = +65^\circ\text{C}$ ,  
 $T_J = 225^\circ\text{C}$  @  $P_{DISS} = 115$  W

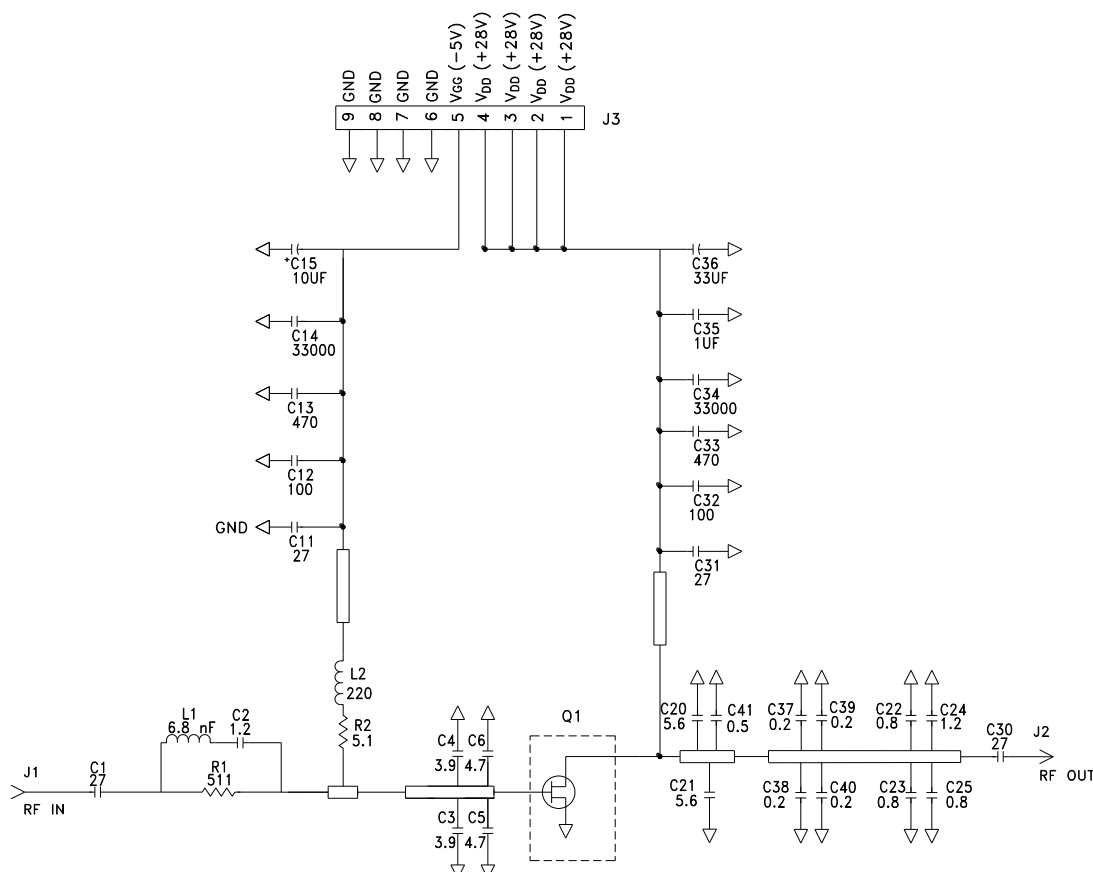
## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

## Evaluation Test Fixture and Recommended Tuning Solution, 1.2 - 1.4 GHz



### Description

Parts measured on evaluation board (32-mil thick RO4003). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

### Biasing Sequence

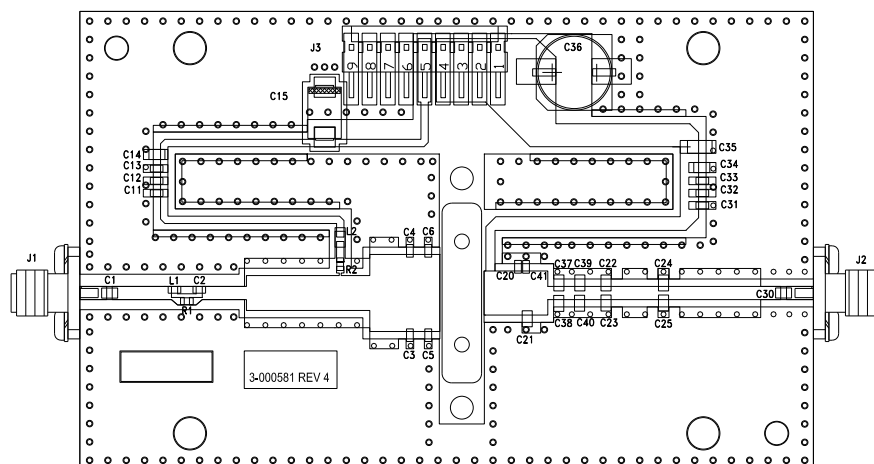
#### Bias ON

1. Ensure RF is turned off
2. Apply pinch-off voltage of -5 V to the gate
3. Apply nominal drain voltage
4. Bias gate to desired quiescent drain current
5. Apply RF

#### Bias OFF

1. Turn RF off
2. Apply pinch-off voltage of -5 V to the gate
3. Turn-off drain voltage
4. Turn-off gate voltage

**Evaluation Test Fixture and Recommended Tuning Solution, 1.2 - 1.4 GHz**



**Assembly Parts List**

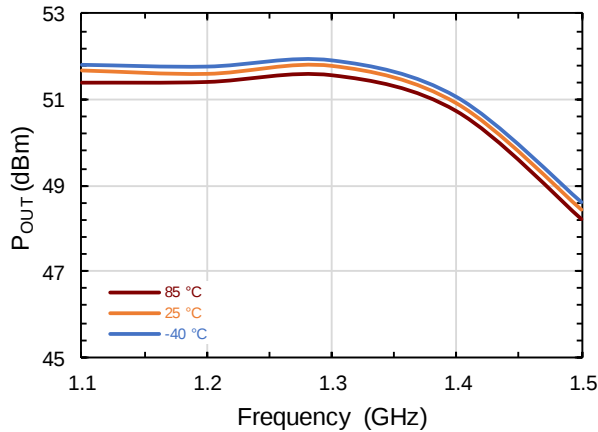
| Reference Designator | Description                                             | Qty. |
|----------------------|---------------------------------------------------------|------|
| C1, C30              | CAP, 27 pF +/- 5%, 250V, 0805, ATC 600F                 | 2    |
| C2                   | CAP, 1.2 pF, +/-0.1pF, 0603, ATC                        | 1    |
| C3, C4               | CAP, 3.9 pF, +/-0.1pF, 0603, ATC                        | 2    |
| C5, C6               | CAP, 4.7 pF, +/-0.1pF, 0603, ATC600S                    | 2    |
| C11, C31             | CAP, 27 pF, +/-5%, 0603, ATC                            | 2    |
| C12, C32             | CAP, 100 pF, +/-5%, 0603, ATC                           | 2    |
| C13, C33             | CAP, 470 pF, 5%, 100V, 0603, X7R, ROHS COMPLIANT        | 2    |
| C14, C34             | CAP, 33000 pF, 0805, 100V, X7R                          | 2    |
| C15                  | CAP, 10 µF 16V TANTALUM, 2312                           | 1    |
| C20                  | CAP, 5.6 pF +/- 0.1 pF, 0505, ATC 800A (Vertical)       | 1    |
| C21                  | CAP, 5.6 pF +/- 0.1 pF, ATC 800B (Vertical)             | 1    |
| C22, C23, C25        | CAP, 0.8 pF +/- 0.05 pF, 0805, ATC 600F                 | 3    |
| C24                  | CAP, 1.2 pF +/- 0.1 pF, 0805, ATC 600F                  | 1    |
| C35                  | CAP, 1 µF, 100V, +/-10%, X7R, 1210                      | 1    |
| C36                  | CAP, 33 µF, 20%, G CASE                                 | 1    |
| C37, C38, C39, C40   | CAP, 0.2 pF +/- 0.05 pF, 0805, ATC 600F                 | 4    |
| C41                  | CAP, 0.5 pF +/- 0.1 pF, 0805, ATC 600F (Vertical)       | 1    |
| L1                   | INDUCTOR, CHIP, 6.8 nH, 0603 SMT                        | 1    |
| L2                   | IND, FERRITE, 220 Ω, 0603                               | 1    |
| R1                   | RES, 1/16W, 0603, 1%, 511 Ω                             | 1    |
| R2                   | RES, 1/16W, 0603, 1%, 5.1 Ω                             | 1    |
| J1, J2               | CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST | 2    |
| J3                   | HEADER RT>PLZ .1CEN LK 9POS                             | 1    |
| -                    | PCB, RO4003, Er = 3.38, h = 32 mil                      | 1    |
| Q1                   | MAPC-A3010-AB                                           | 1    |

**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

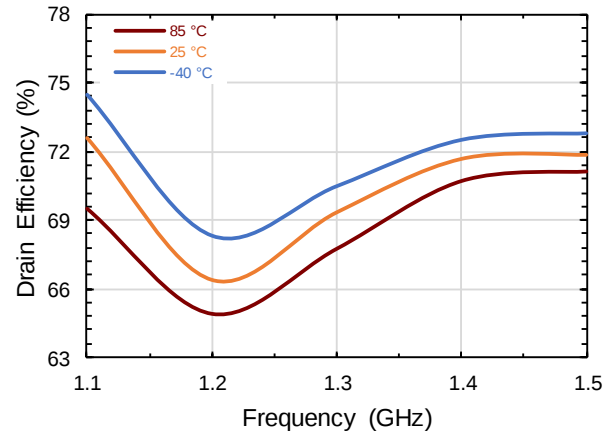
CW,  $P_{SAT}$  measurements @  $I_{GS} = 2.88$  mA,  $V_{DS} = 28$  V,  $I_{DQ} = 1$  A, Freq = 1.3 GHz (Unless Otherwise Noted)

For Engineering Evaluation Only – This data does not Modify MACOM's Datasheet Limits.

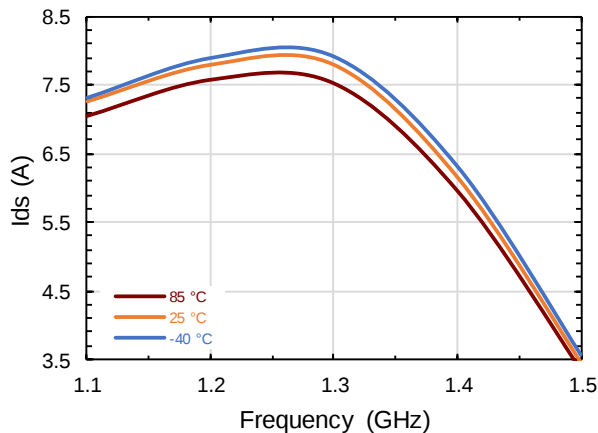
**Output Power vs. Temperature and Frequency**



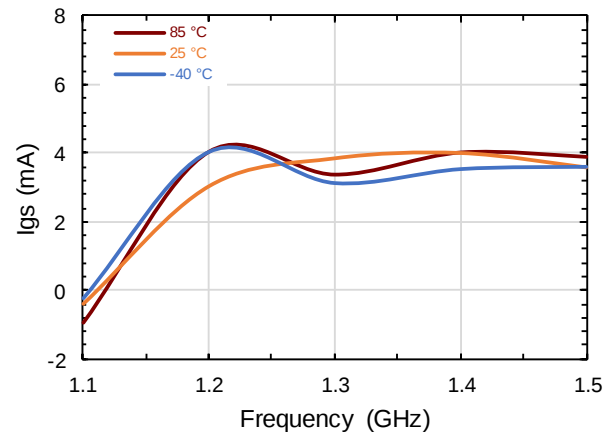
**Drain Efficiency vs. Temperature and Frequency**



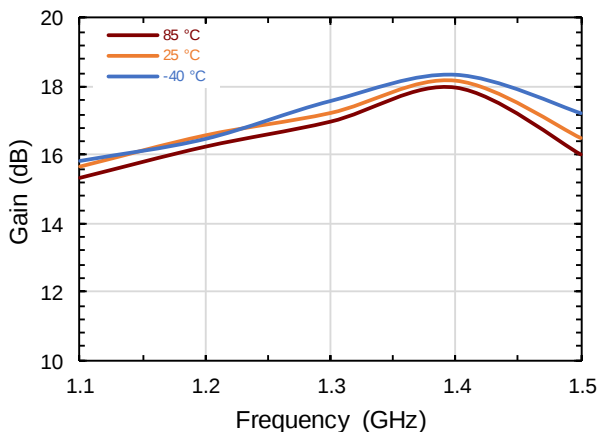
**Drain Current vs. Temperature and Frequency**



**Gate Current vs. Temperature and Frequency**



**Large Signal Gain vs. Temperature and Frequency**

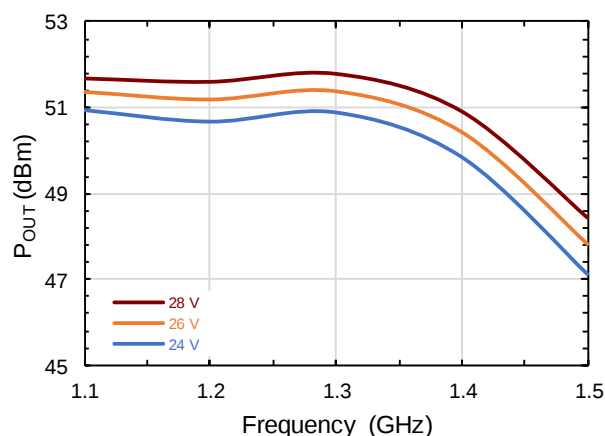


# Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture

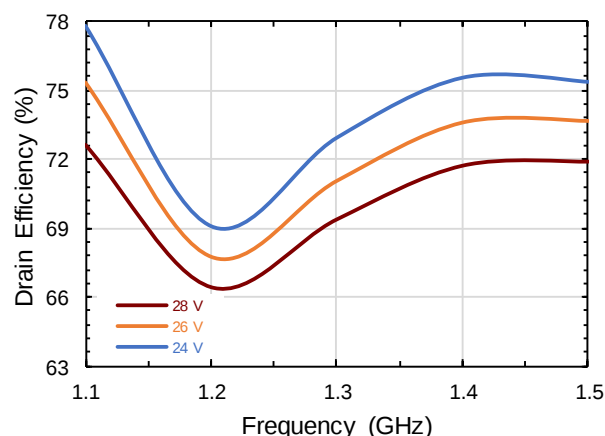
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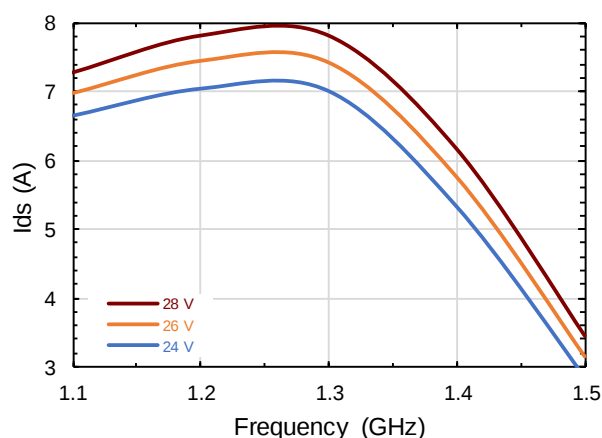
**Output Power vs.  $V_{DS}$  and Frequency**



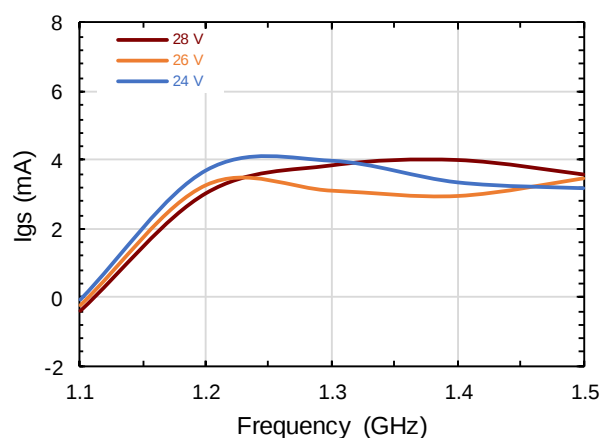
**Drain Efficiency vs.  $V_{DS}$  and Frequency**



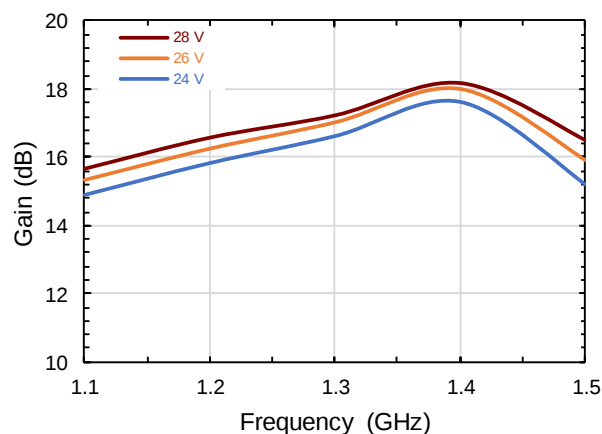
**Drain Current vs.  $V_{DS}$  and Frequency**



**Gate Current vs.  $V_{DS}$  and Frequency**



**Large Signal Gain vs.  $V_{DS}$  and Frequency**

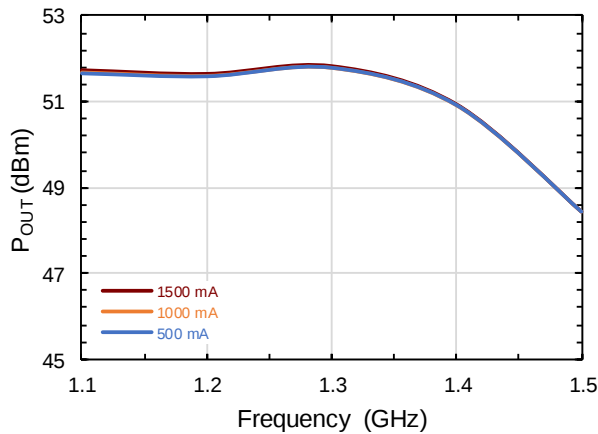


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

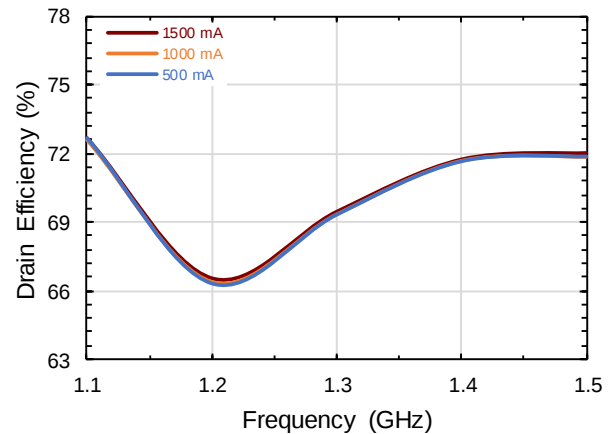
CW,  $P_{SAT}$  measurements @  $I_{GS} = 2.88$  mA,  $V_{DS} = 28$  V,  $I_{DQ} = 1$  A, Freq = 1.3 GHz (Unless Otherwise Noted)

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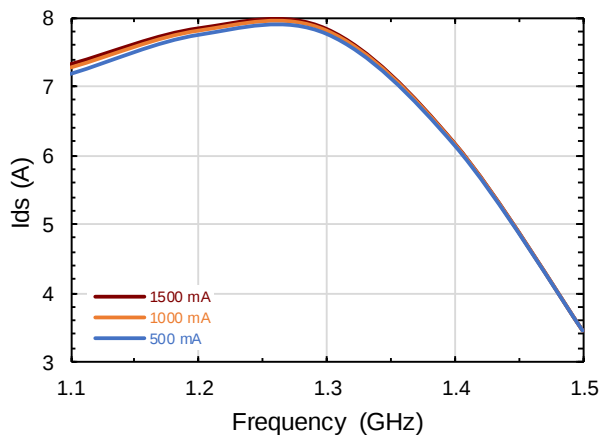
**Output Power vs.  $I_{DQ}$  and Frequency**



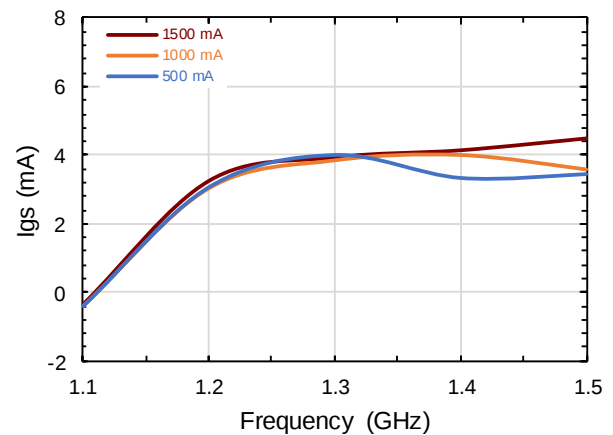
**Drain Efficiency vs.  $I_{DQ}$  and Frequency**



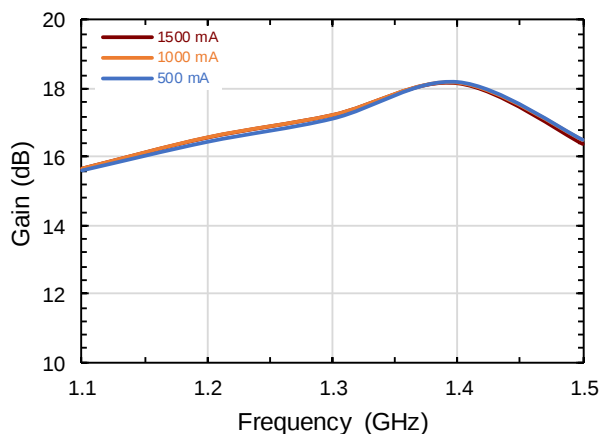
**Drain Current vs.  $I_{DQ}$  and Frequency**



**Gate Current vs.  $I_{DQ}$  and Frequency**



**Large Signal Gain vs.  $I_{DQ}$  and Frequency**

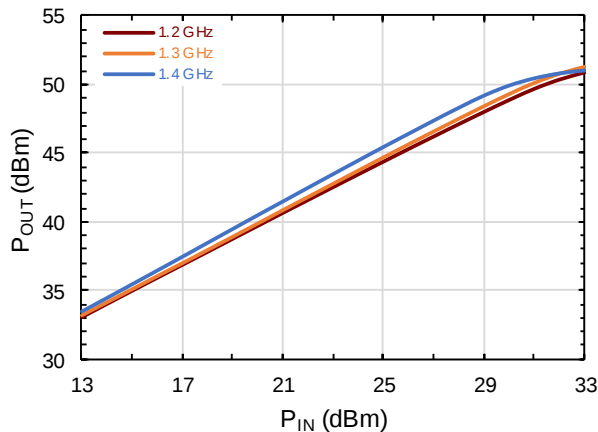


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

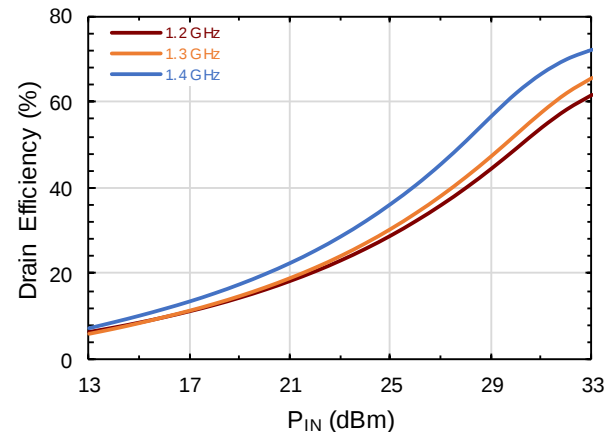
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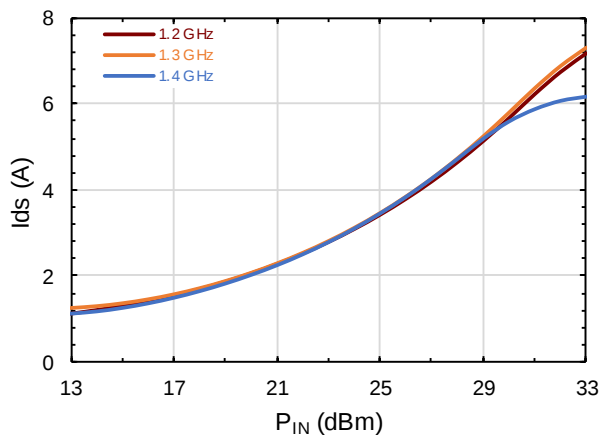
**Output Power vs. Frequency and  $P_{IN}$**



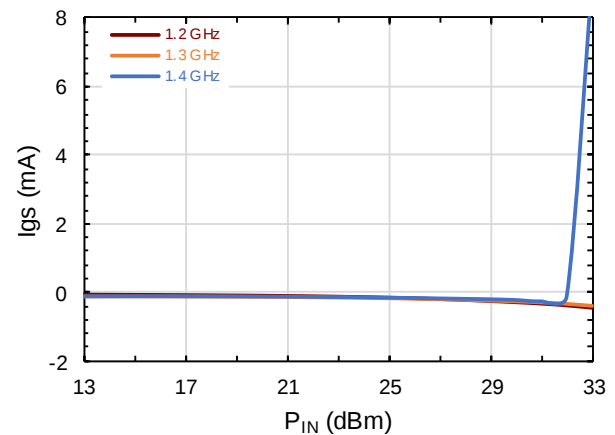
**Drain Efficiency vs. Frequency and  $P_{IN}$**



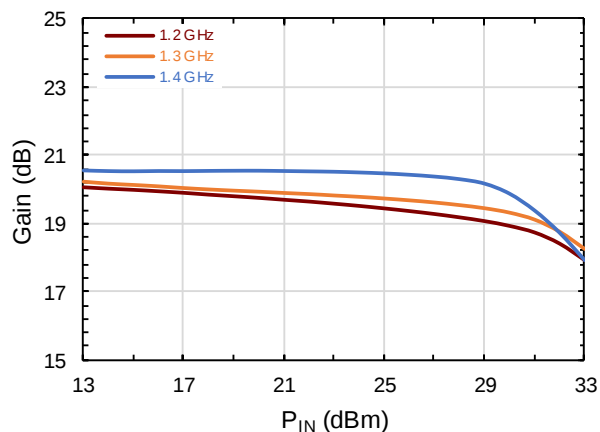
**Drain Current vs. Frequency and  $P_{IN}$**



**Gate Current vs. Frequency and  $P_{IN}$**



**Large Signal Gain vs. Frequency and  $P_{IN}$**

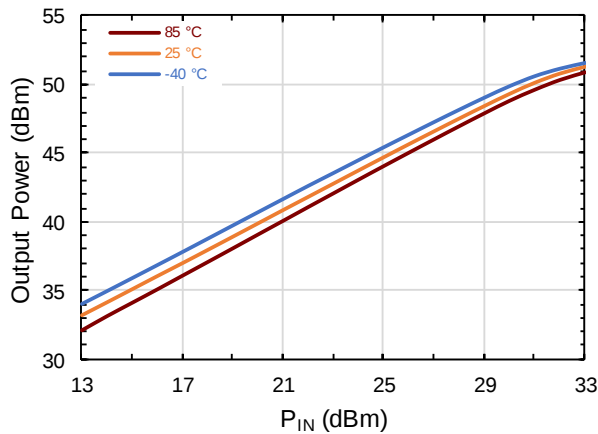


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

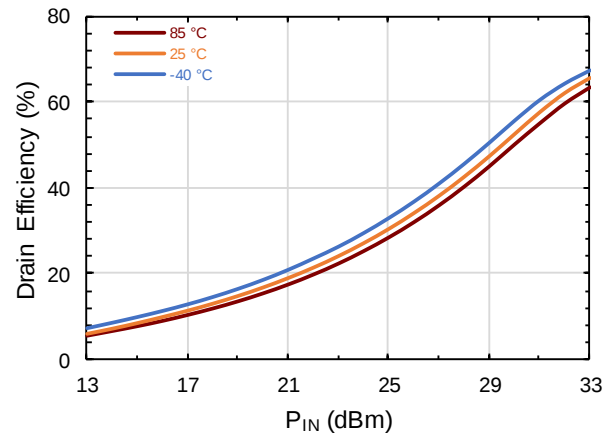
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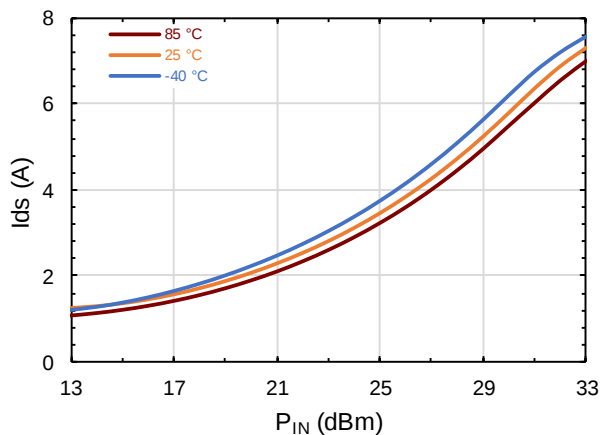
**Output Power vs. Temperature and  $P_{IN}$**



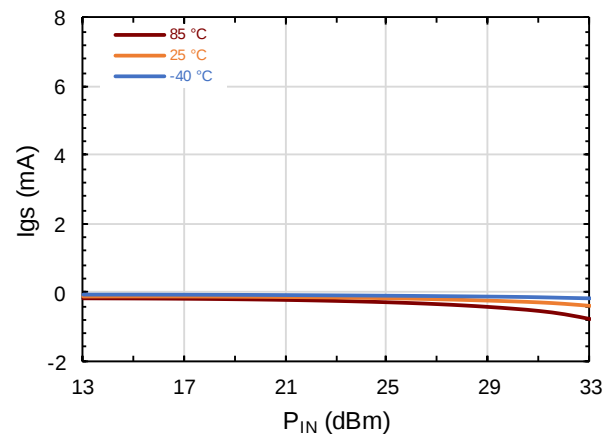
**Drain Efficiency vs. Temperature and  $P_{IN}$**



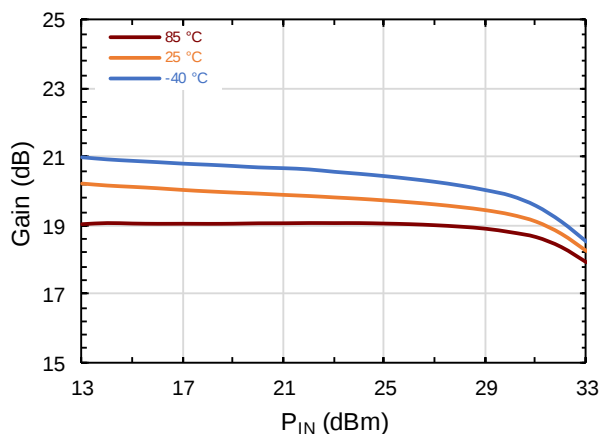
**Drain Current vs. Temperature and  $P_{IN}$**



**Gate Current vs. Temperature and  $P_{IN}$**



**Large Signal Gain vs. Temperature and  $P_{IN}$**

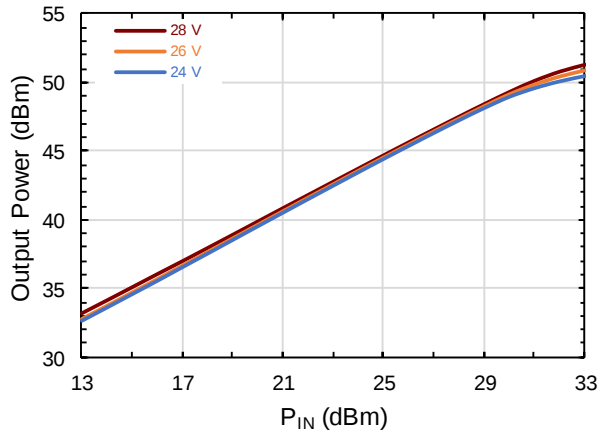


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

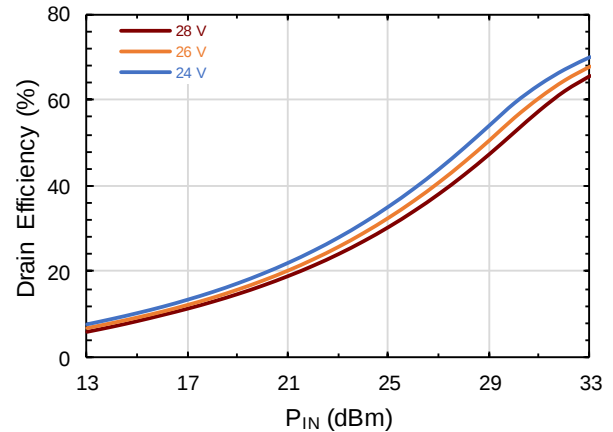
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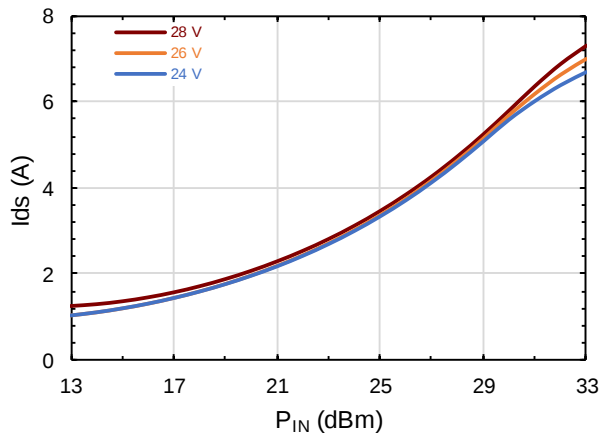
**Output Power vs.  $V_{DS}$  and  $P_{IN}$**



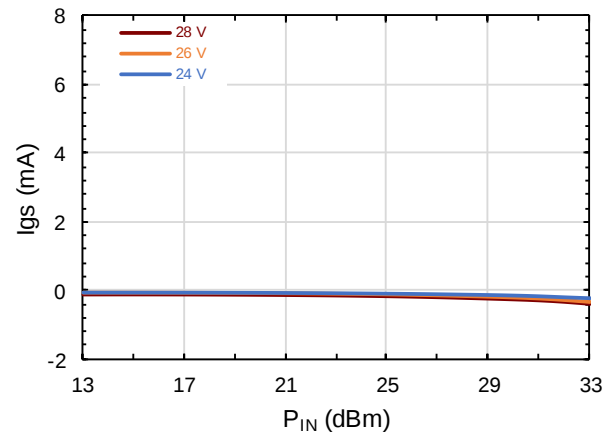
**Drain Efficiency vs.  $V_{DS}$  and  $P_{IN}$**



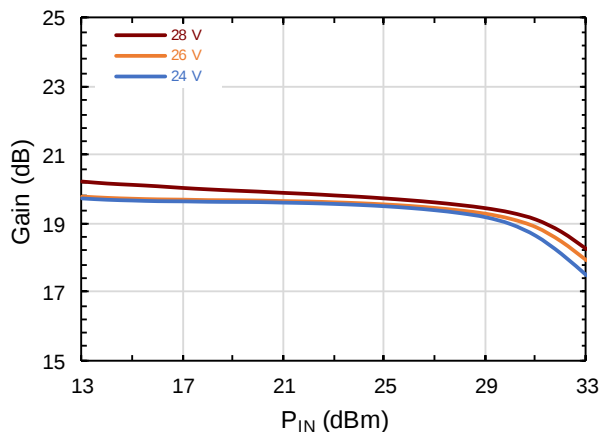
**Drain Current vs.  $V_{DS}$  and  $P_{IN}$**



**Gate Current vs.  $V_{DS}$  and  $P_{IN}$**



**Large Signal Gain vs.  $V_{DS}$  and  $P_{IN}$**

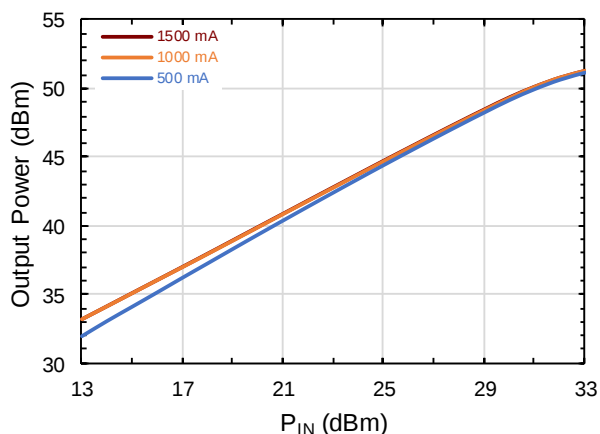


# Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture

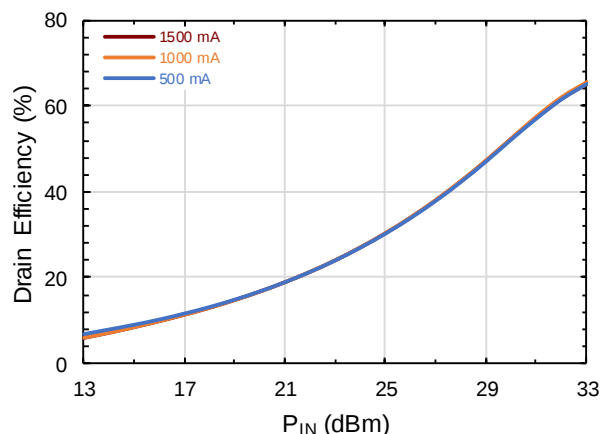
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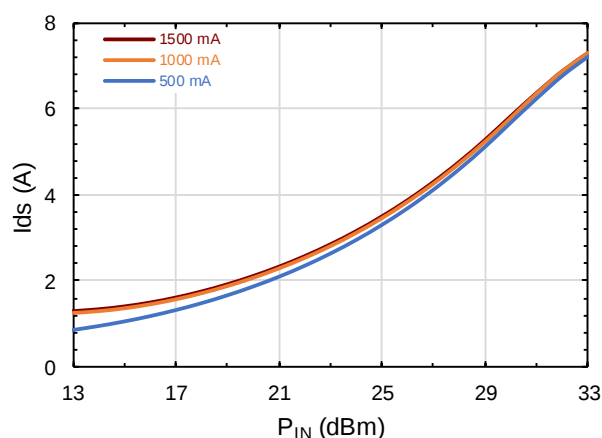
**Output Power vs.  $I_{DQ}$  and  $P_{IN}$**



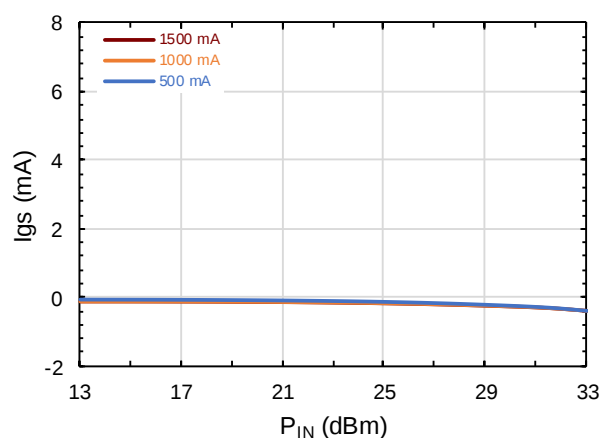
**Drain Efficiency vs.  $I_{DQ}$  and  $P_{IN}$**



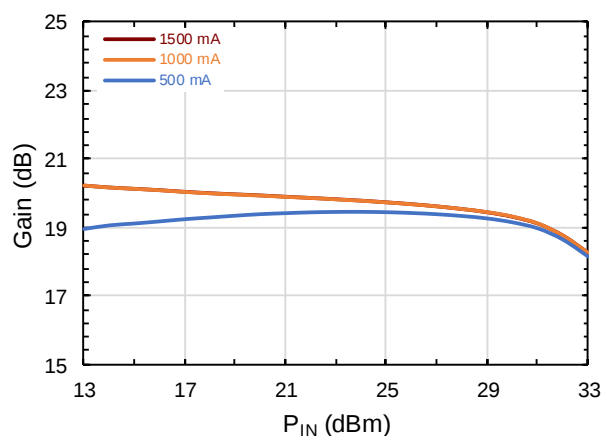
**Drain Current vs.  $I_{DQ}$  and  $P_{IN}$**



**Gate Current vs.  $I_{DQ}$  and  $P_{IN}$**



**Large Signal Gain vs.  $I_{DQ}$  and  $P_{IN}$**

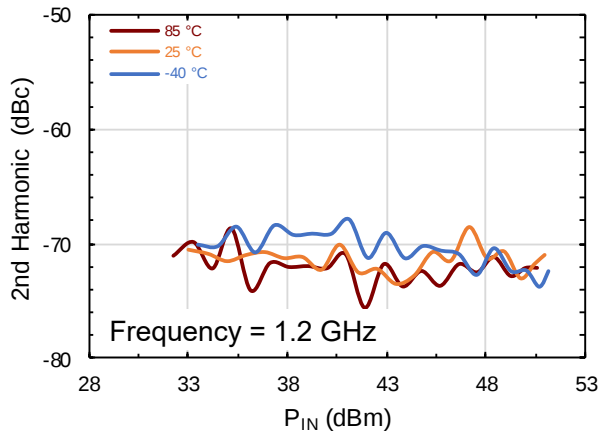


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture**

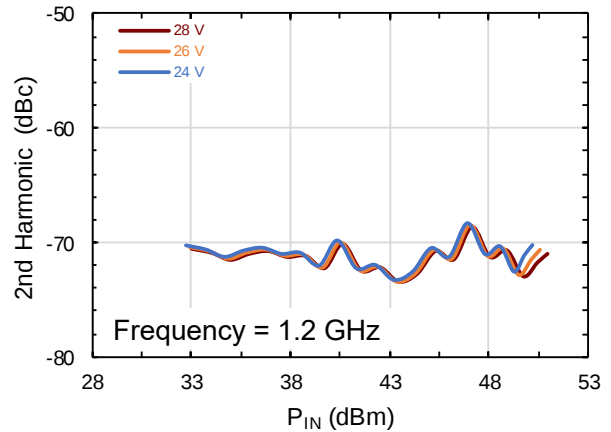
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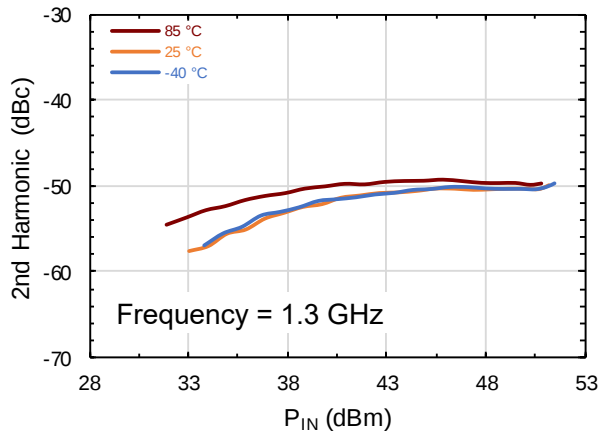
**2<sup>nd</sup> Harmonic vs. Temperature and  $P_{IN}$**



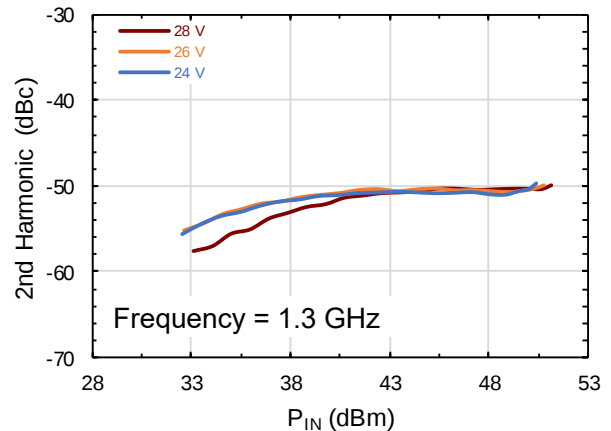
**2<sup>nd</sup> Harmonic vs.  $V_{DS}$  and  $P_{IN}$**



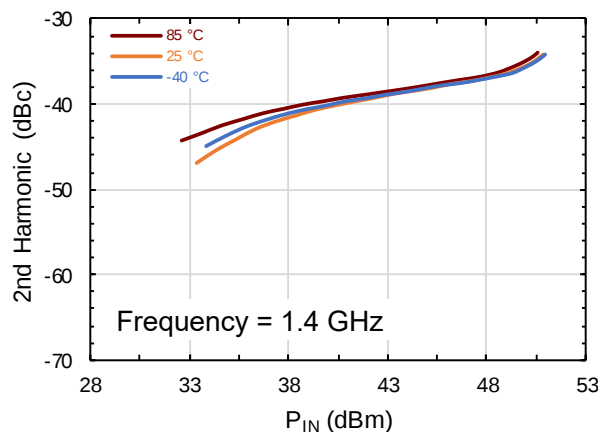
**2<sup>nd</sup> Harmonic vs. Temperature and  $P_{IN}$**



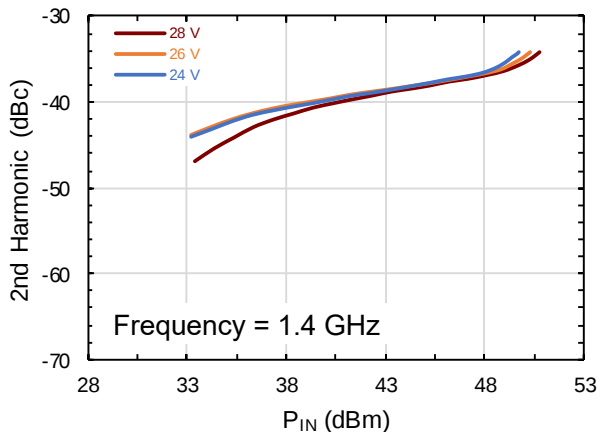
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**2<sup>nd</sup> Harmonic vs. Temperature and  $P_{IN}$**

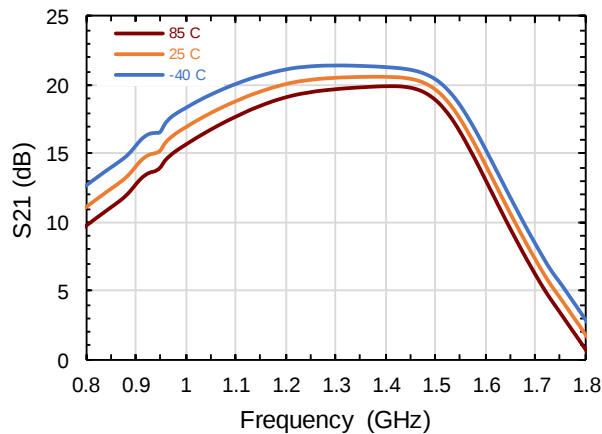


**2<sup>nd</sup> Harmonic vs.  $V_{DS}$  and  $P_{IN}$**

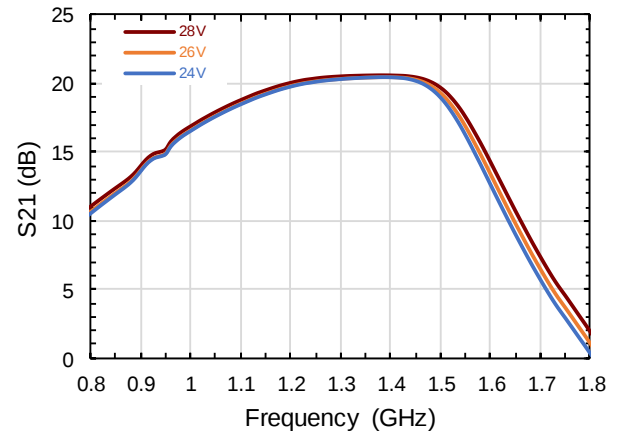


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture:**  
CW,  $V_{DS} = 28$  V,  $I_{DQ} = 1000$  mA,  $P_{in} = -20$  dBm (Unless Otherwise Noted)  
For Engineering Evaluation Only—This data does not Modify MACOM's Datasheet Limits.

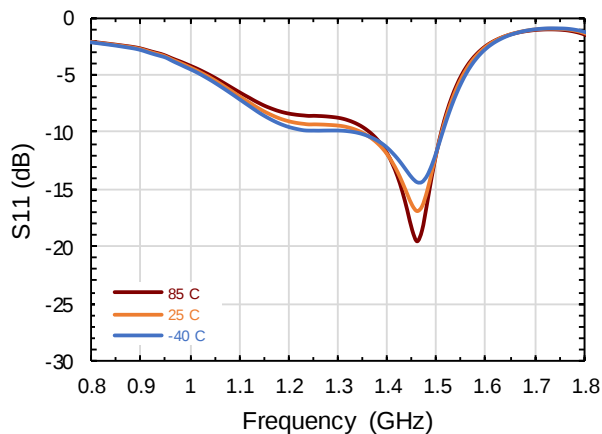
**S21 vs Frequency and Temperature**



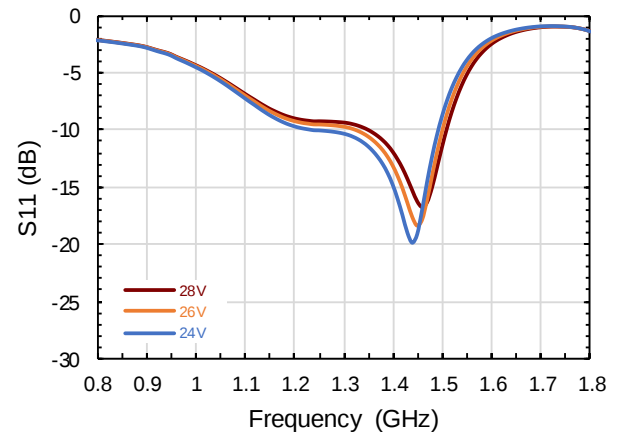
**S21 vs Frequency and  $V_{DS}$**



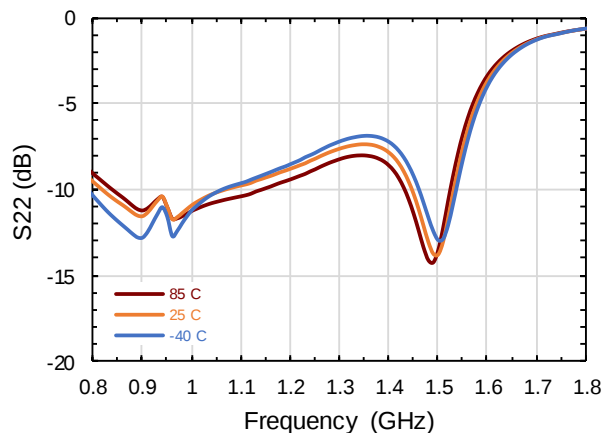
**S11 vs Frequency and Temperature**



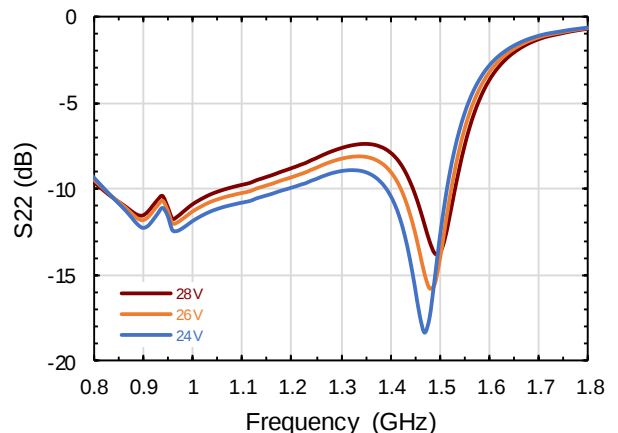
**S11 vs Frequency and  $V_{DS}$**



**S22 vs Frequency and Temperature**



**S22 vs Frequency and  $V_{DS}$**

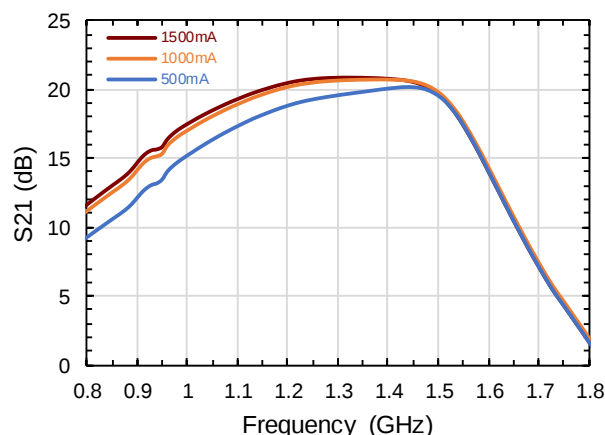


**Typical Performance Curves as Measured in the 1.2– 1.4 GHz Evaluation Test Fixture:**

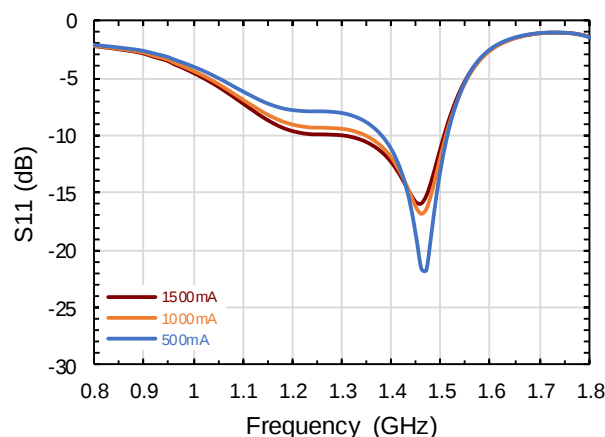
CW,  $V_{DS} = 28$  V,  $I_{DQ} = 1000$  mA,  $P_{in} = -20$  dBm (Unless Otherwise Noted)

For Engineering Evaluation Only—This data does not Modify MACOM's Datasheet Limits.

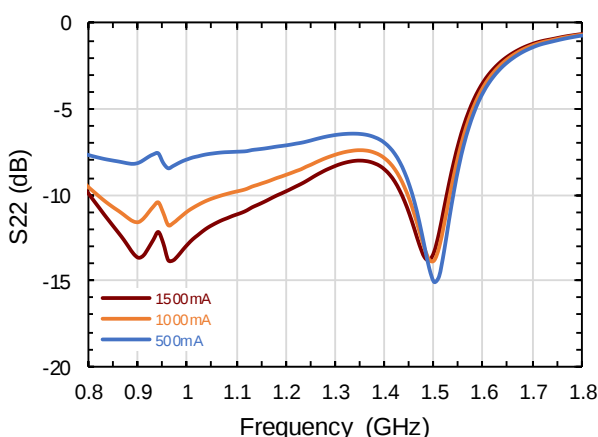
***S<sub>21</sub> vs Frequency and  $I_{DQ}$***



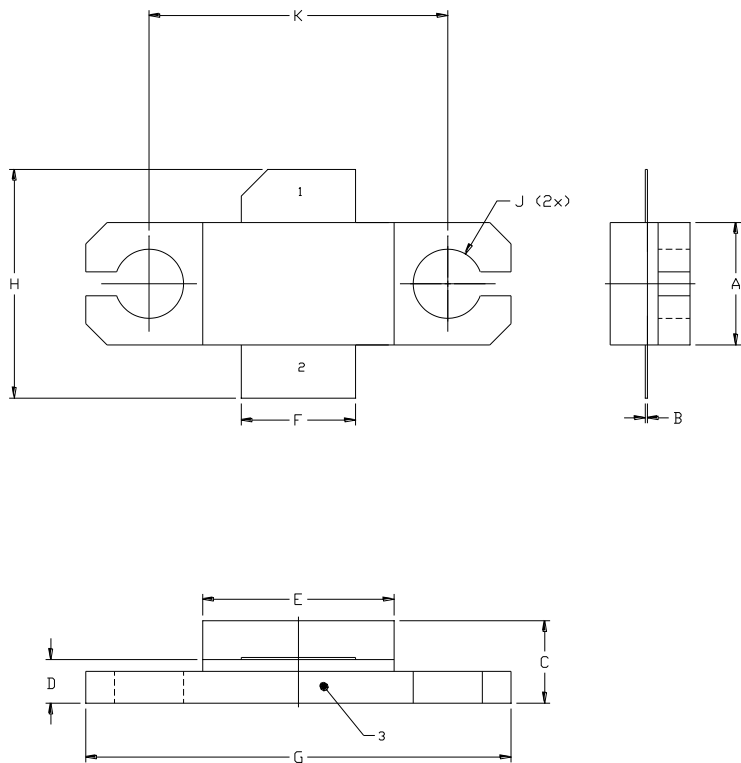
***S<sub>11</sub> vs Frequency and  $I_{DQ}$***



***S<sub>22</sub> vs Frequency and  $I_{DQ}$***



Lead-free 440223 Package Dimensions



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
  4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
  5. ALL PLATED SURFACES ARE Ni/AU.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.225  | 0.235 | 5.72        | 5.97  |
| B   | 0.004  | 0.006 | 0.10        | 0.15  |
| C   | 0.145  | 0.165 | 3.68        | 4.19  |
| D   | 0.077  | 0.087 | 1.96        | 2.21  |
| E   | 0.355  | 0.365 | 9.02        | 9.27  |
| F   | 0.210  | 0.220 | 5.33        | 5.59  |
| G   | 0.795  | 0.805 | 20.19       | 20.45 |
| H   | 0.400  | 0.460 | 10.16       | 11.68 |
| J   | Ø .130 |       | 3.30        |       |
| k   | 0.562  |       | 14.27       |       |

PIN 1. GATE  
PIN 2. DRAIN  
PIN 3. SOURCE

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